

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office						Atty. Docket No. 0980/64609-Z	Serial No. 10/106,991
INFORMATION DISCLOSURE CITATION BY APPLICANT (Use several sheets if necessary)								Applicant Zuhua Zhu, et al.	
								Filing Date March 26, 2002	Group 2812
U.S. PATENT DOCUMENTS									
Examiner Initial		Document Number		Date	Name	Class	Subclass	Filing Date if Appropriate	
PN		AA	5 2 5 6 5 9 6	10/26/93	Ackley et al.				
		AB	5 2 5 8 3 1 6	11/02/93	Ackley et al.				
		AC	5 5 5 7 6 2 7	09/17/96	Schneidner, Jr. et al.				
		AD	5 5 5 9 0 5 3	09/24/96	Choquette et al.				
		AE	5 7 2 4 3 7 6	03/03/98	Kish, Jr. et al.				
		AF	5 8 3 1 2 9 5	11/03/98	Huang et al.				
		AG	5 8 3 7 5 6 1	11/17/98	Kish, Jr. et al.				
		AH	5 9 8 5 6 8 6	11/16/99	Jayaraman				
		AI	6 1 6 0 8 3 0	12/12/00	Kiely et al.				
		AJ	6 1 6 9 7 5 6	01/02/01	Chirovsky et al.				
FOREIGN PATENT DOCUMENTS									
		Document Number		Date	Country	Class	Subclass	Translation	
								Yes	No
	AK								
	AL								
	AM								
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
PN	AN	Choquette, "The Technology of Selectively Oxidized Vertical Cavity Lasers," at Chapter 2 of Cheng and Dutta, eds., <i>Vertical-Cavity Surface-Emitting Lasers: Technology and Applications, Vol. 10 of Optoelectronic Properties of Semiconductors and Superlattices</i> , Manasreh, ed., Gordon and Breach Science Publishers (2000).							
	AO	Chua, C.L. et. al., "Planar laterally oxidized vertical-cavity lasers for low-threshold high-density top-surface-emitting arrays," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 8, pp. 1060-2 (August 1997)							
✓	AP	Deppe, "Optoelectronic Properties of Semiconductors and Superlattices," at Chapter 1 of Cheng and Dutta, eds., <i>Vertical-Cavity Surface-Emitting Lasers: Technology and Applications, Vol. 10 of Optoelectronic Properties of Semiconductors and Superlattices</i> , Manasreh, ed., Gordon and Breach Science Publishers (2000).							
EXAMINER <i>Phillip Nguyen</i>		DATE CONSIDERED <i>3/1/04</i>							
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

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Examiner Initial		Document Number						Date	Name	Class	Subclass	Filing Date if Appropriate
PN	AA	6	4	6	5	8	1	1	10/15/02	Peters et al.		
	AB											
	AC											
	AD											
	AE											
	AF											

FOREIGN PATENT DOCUMENTS

		Document Number						Date	Country	Class	Subclass	Translation	
												Yes	No
	AG												
	AH												

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

PN	AI	Deppe et al., "Low-threshold vertical cavity surface emitting lasers based on oxide confinement and high contrast distributed Bragg reflectors," IEEE Journal of Selected Topics in Quantum Electronics, vol. 3, no. 3, pp. 893-904 (June 1997).
	AJ	Dutton, Understanding Optical Communications (Prentice Hall 1998), at pp. 159-161.
	AK	Jewell et. al., "Vertical cavity surface emitting lasers: design, growth, fabrication, characterization", IEEE Journal of Quantum Electronics, vol. 27, no. 6, pp. 1332-1346 (June 1991).
	AL	Nishiyama et. al., "Multi-oxide layer structure for single mode operation in vertical cavity surface emitting lasers," IEEE Photonics Technology Letters, vol. 12, no. 6, pp. 606-8 (June 2000).
	AM	Sale, T.E., Vertical Cavity Surface Emitting Lasers, Wiley & Sons (1995)

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